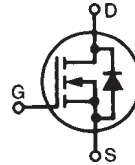


# Polar3™ HiPerFET™ Power MOSFET

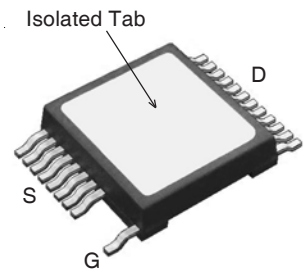
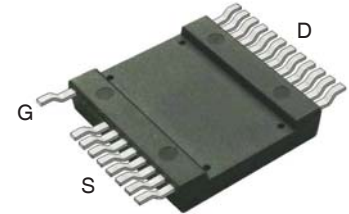
## MMIX1F132N50P3

$V_{DSS} = 500V$   
 $I_{D25} = 63A$   
 $R_{DS(on)} \leq 43m\Omega$   
 $t_{rr} \leq 250ns$

(Electrically Isolated Tab)



N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier



G = Gate    D = Drain  
S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	63	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	330	A
$I_A$	$T_C = 25^\circ C$	66	A
$E_{AS}$	$T_C = 25^\circ C$	2	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	35	V/ns
$P_D$	$T_C = 25^\circ C$	520	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$V_{ISOL}$	50/60 Hz, 1 Minute	2500	V~
$F_C$	Mounting Force	50..200 / 11..45	N/lb
<b>Weight</b>		8	g

### Features

- Silicon Chip on Direct-Copper-Bond Substrate
  - High Power Dissipation
  - Isolated Mounting Surface
  - 2500V~ Electrical Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$

### Advantages

- Easy to Mount
- Space Savings

### Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ Note 2, $T_J = 125^\circ C$			50 $\mu A$ 3 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 66A$ , Note 1			43 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1	68	110	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		18.6	nF
$C_{oss}$			1710	pF
$C_{rss}$			12	pF
$R_{Gi}$	Gate Input Resistance		1.16	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 66\text{A}$ $R_G = 1\Omega$ (External)		42	ns
$t_r$			19	ns
$t_{d(off)}$			90	ns
$t_f$			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 66\text{A}$		267	nC
$Q_{gs}$			95	nC
$Q_{gd}$			63	nC
$R_{thJC}$				0.24 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$
$R_{thJA}$		30		$^\circ\text{C/W}$

**Source-Drain Diode**

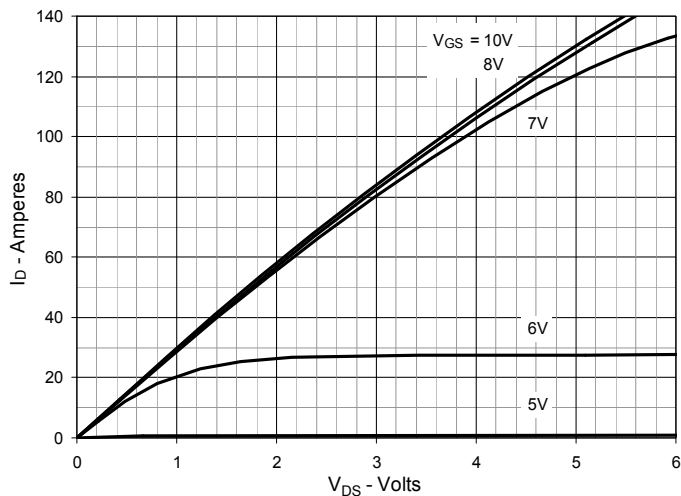
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			132 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			530 A
$V_{SD}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 66\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			250 ns
$Q_{RM}$			1.9	$\mu\text{C}$
$I_{RM}$			16.4	A

**Notes:**

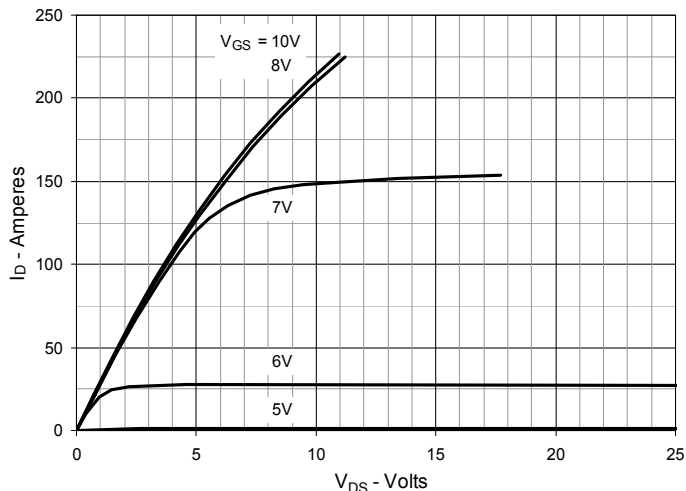
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Part must be heatsunk for high-temp  $I_{DSS}$  measurement.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

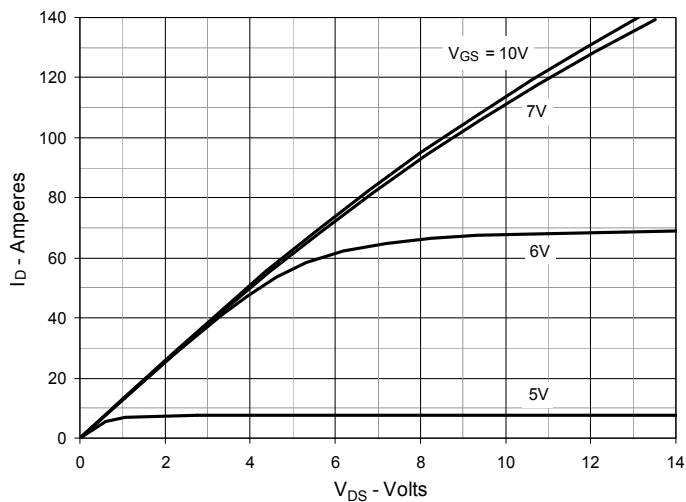
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



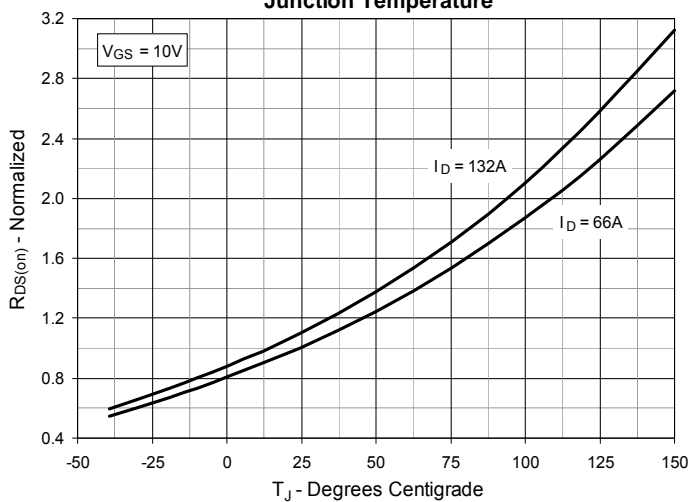
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



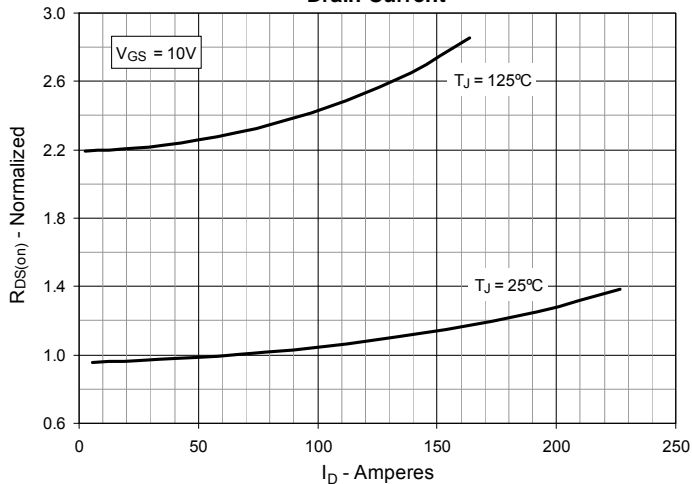
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



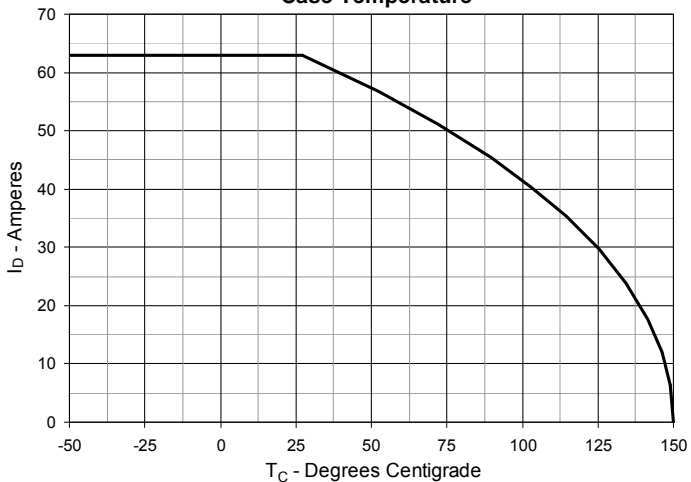
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 66\text{A}$  Value vs. Junction Temperature**



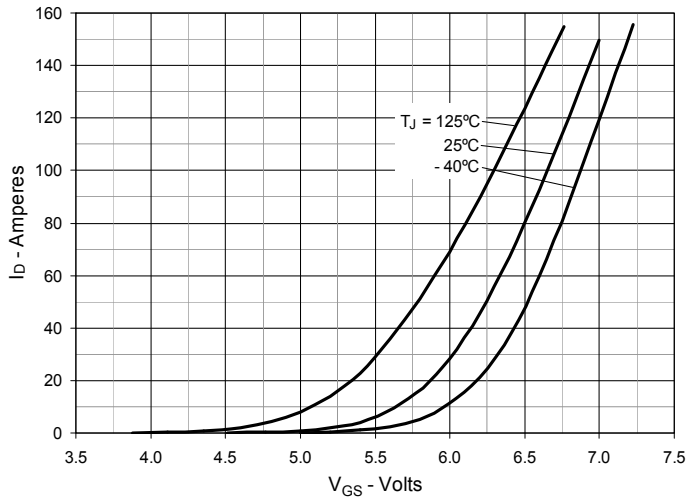
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 66\text{A}$  Value vs. Drain Current**



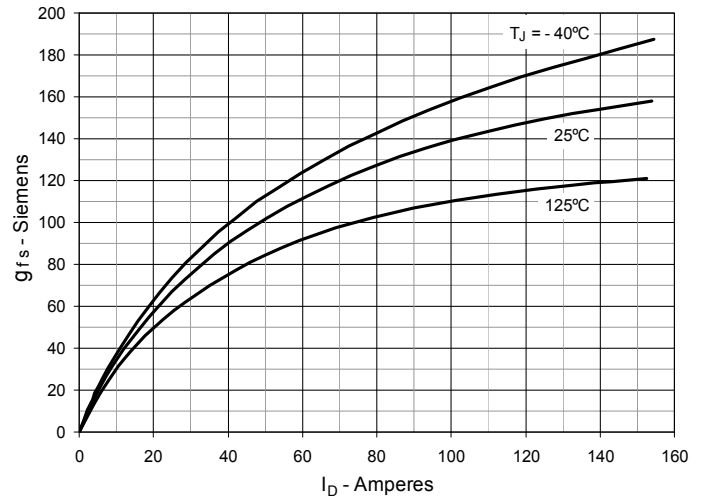
**Fig. 6. Maximum Drain Current vs. Case Temperature**



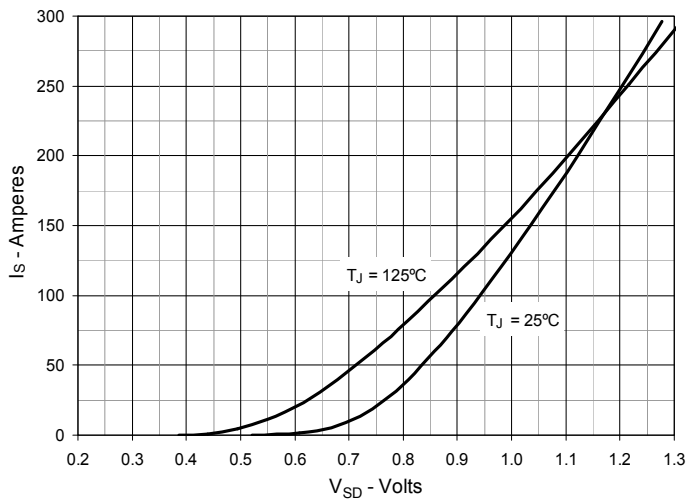
**Fig. 7. Input Admittance**



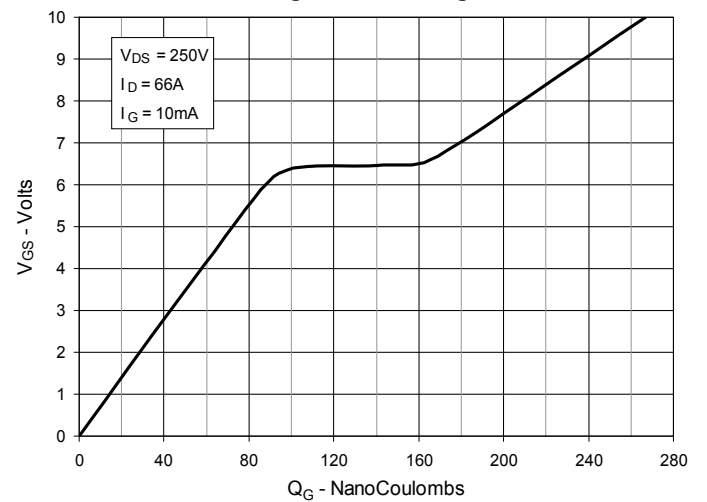
**Fig. 8. Transconductance**



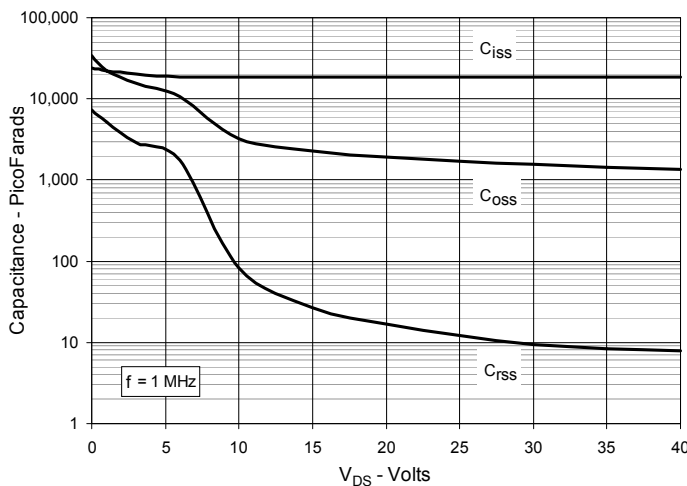
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



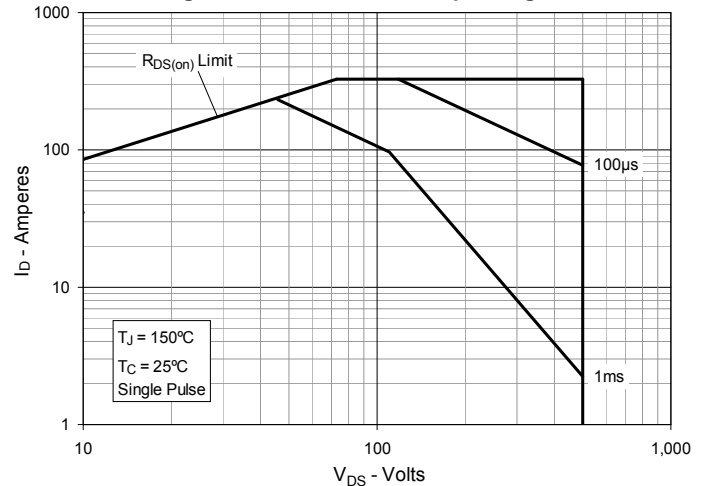
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



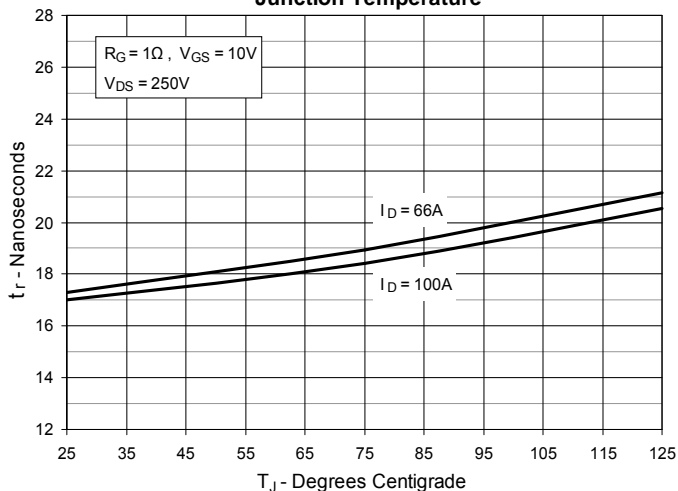
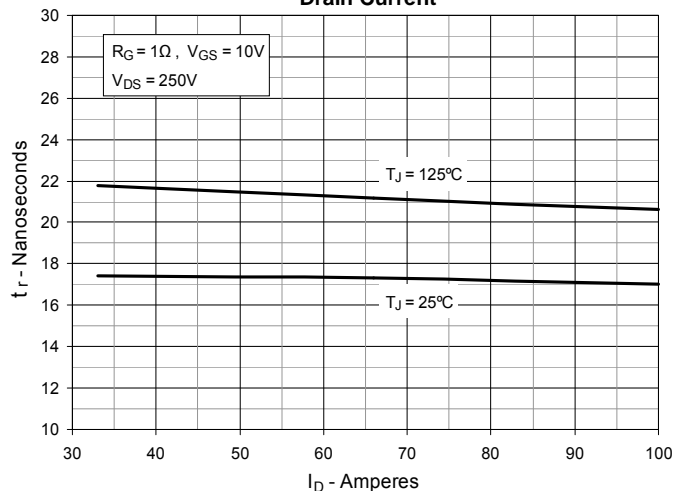
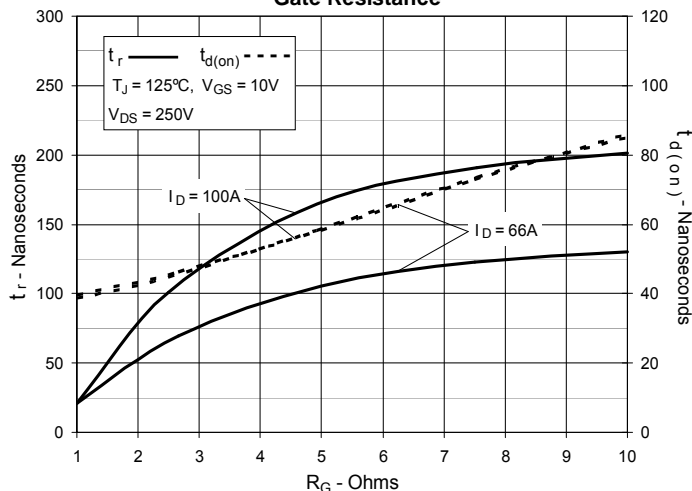
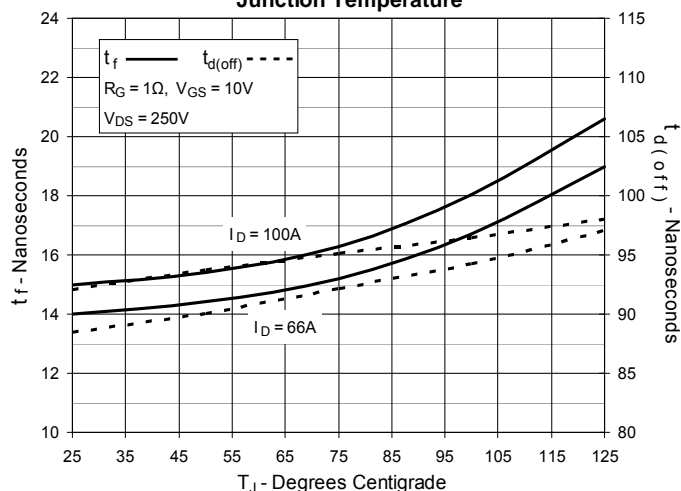
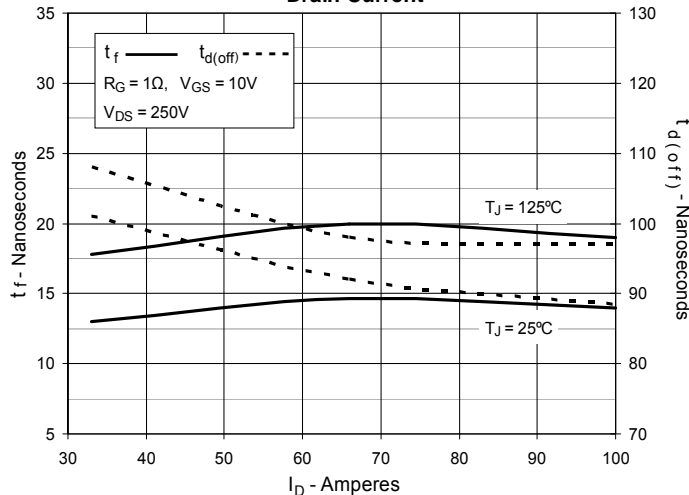
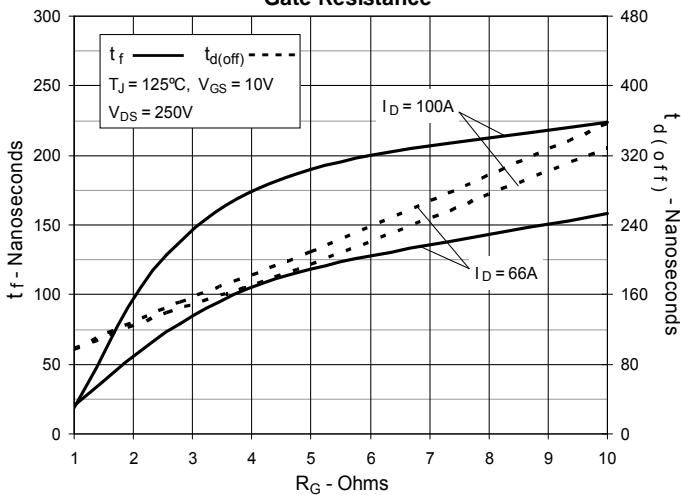
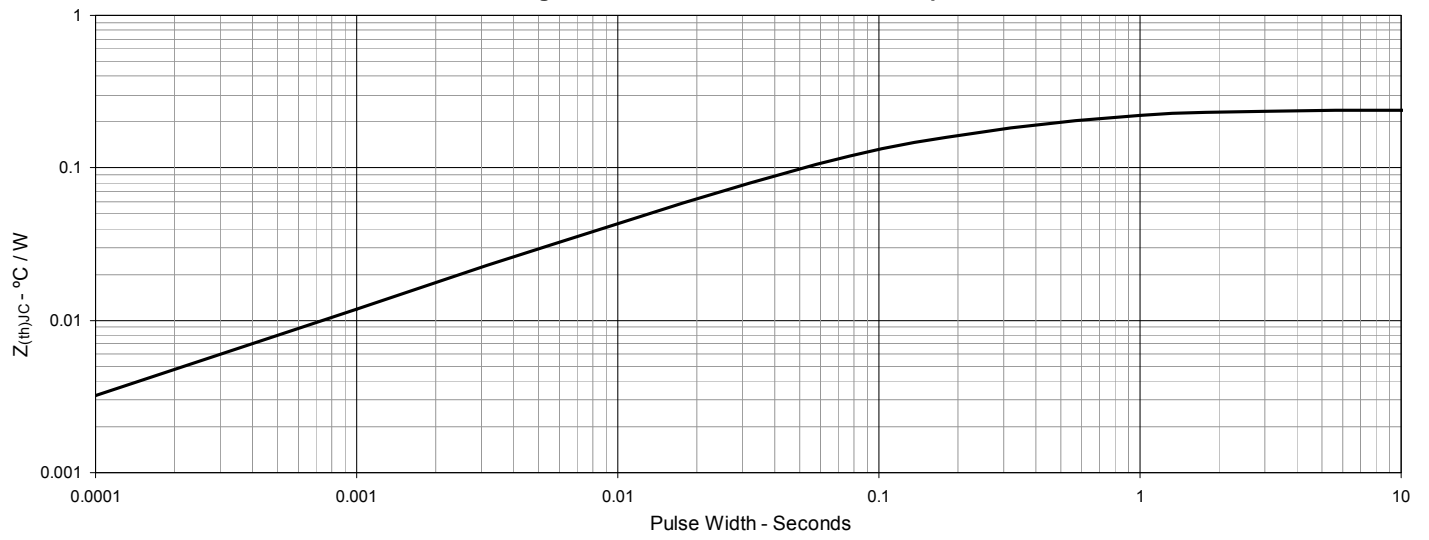
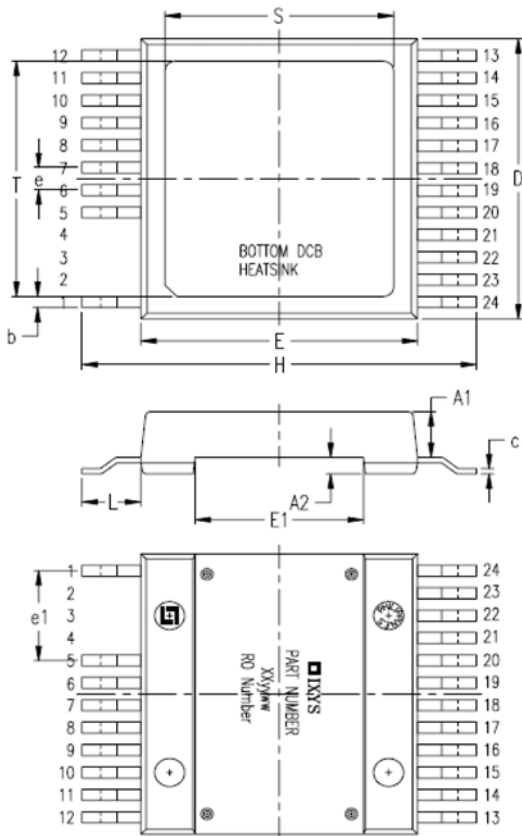
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**

**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**

**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**

**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**

**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**

**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**


Fig. 19. Maximum Transient Thermal Impedance



## Package Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.976	.994	24.80	25.25
E	.898	.915	22.80	23.25
E1	.543	.559	13.80	14.20
e	.079 BSC		2.00 BSC	
e1	.315 BSC		8.00 BSC	
H	1.272	1.311	32.30	33.30
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.736	.760	18.70	19.30
T	.815	.839	20.70	21.30
∞	0	4'	0	4'

PIN: 1 = Gate  
 5-12 = Source  
 13-24 = Drain